

| L Number | Hits | Search Text  | DB  | Time stamp       |
|----------|------|--|---|------------------|
| 1        | 41   | (257/645).CCLS.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/05/13 17:26 |
| 2        | 2    | ((257/645).CCLS.) and trap with (density carrier impurity holes electron) same nitride   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/05/13 16:45 |
| 3        | 182  | (257/\$).ccls. and trap with (density carrier impurity holes electron) same nitride  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/05/13 17:02 |
| 4        | 154  | control with gate and trap with (density carrier impurity holes electron) same nitride   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/05/13 17:01 |
| 5        | 83   | (control with gate and trap with (density carrier impurity holes electron) same nitride) not ((257/\$).ccls. and trap with (density carrier impurity holes electron) same nitride) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/05/13 17:02 |
| 6        | 3    | 5907183.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/05/13 17:27 |
| 7        | 3    | 5731238.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/05/13 17:27 |
| -        | 18   | insulation with layer with trap with density   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/05/13 10:55 |
| -        | 5    | floating adj gate with trap adj density  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/05/11 12:02 |
| -        | 6    | ("4154873"   "4331709"   "4447272"   "5010024"   "5017979"   "5019533").PN.  | USPAT   | 2002/05/10 16:23 |
| -        | 135  | (silicon adj oxide silicon adj nitride insulating insulator flating adj gate control adj gate ONO NON)with trap adj density  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/05/11 12:20 |
| -        | 26   | silicon adj nitride with trap adj density  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/05/11 14:38 |
| -        | 8    | silicon adj nitride with trap adj density same hydrogen  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/05/11 14:38 |
| -        | 3    | 5731238.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM TDB | 2002/05/13 11:02 |

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| - | 174     | hydrogen with NON with insulating  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 11:04 |
| - | 2       | (hydrogen with NON with insulating) and floating with gate                                       | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 11:03 |
| - | 31      | (hydrogen with NON with insulating) and nitride with hydrogen                                    | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 11:07 |
| - | 82      | silicon with nitride with hydrogen and floating with gate  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 11:18 |
| - | 7       | ("4688078"   "4788082"   "5256205"   "5356672"   "5356673"   "5368897"   "5403399").PN.          | USPAT   | 2002/05/13 11:14 |
| - | 3       | 5483097.pn.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 11:39 |
| - | 4       | 5483097.URPN.  | USPAT   | 2002/05/13 11:18 |
| - | 1009419 | silicon adj nitride wiht density   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 11:43 |
| - | 33960   | (silicon adj nitride wiht density) and (257/\$).ccls.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 11:40 |
| - | 43257   | (silicon adj nitride wiht density) and inter ajd layer and floating with gate and (257/\$).ccls. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 11:41 |
| - | 95      | (silicon adj nitride wiht density) and inter adj layer and floating with gate and (257/\$).ccls. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 11:43 |
| - | 2498    | silicon adj nitride with density   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 11:43 |
| - | 1       | (silicon adj nitride with density) and inter adj layer and floating with gate and (257/\$).ccls. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 11:44 |
| - | 32      | (silicon adj nitride with density) and floating with gate and (257/\$).ccls.                     | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 11:49 |
| - | 63      | silicon adj nitride adj density  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 12:10 |

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| - | 8  | thermal with nitr\$8 same trap adj density     | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 12:12 |
| - | 8  | thermal with nitr\$ same trap adj density      | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 12:13 |
| - | 0  | thermal with nitrization same trap adj density | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 12:14 |
| - | 0  | thermal with nitrization and trap adj density  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 12:14 |
| - | 30 | thermal with nitrization                       | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/05/13 16:41 |